Silicon NPN Power Transistors 2SC2371

DESCRIPTION

- With TO-126 package
- High Voltage
- High frequency

APPLICATIONS

- For TV chroma output and vertical output applications

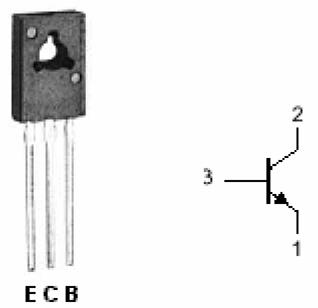

Fig.1 simplified outline (TO-126) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		0.1	A
I_{CM}	Collector current-peak		0.2	A
P_C	Collector power dissipation	T_a=25℃	1.25	W
		T_C=25℃	10	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-40~150	℃

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=30mA ;I_B=3m A			1.5	V
V_{BE}	Base-emitter on voltage	I_C=10mA ; V_{CE}=10V			1.2	V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=100 µ A;I_E=0	300			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA; I_B=0	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=100 µ A; I_C=0	6			V
h_{FE}	DC current gain	I_C=10mA ; V_{CE}=10V	40		250	
I_{CBO}	Collector cut-off current	V_{CB}=200V; I_E=0			0.1	µ A
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			0.1	µ A
C_{OB}	Output capacitance	I_E=0; V_{CB}=30V;f=1MHz		3		pF
f_T	Transition frequency	I_E=10mA ; V_{CB}=30V	50			MHz

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PACKAGE OUTLINE

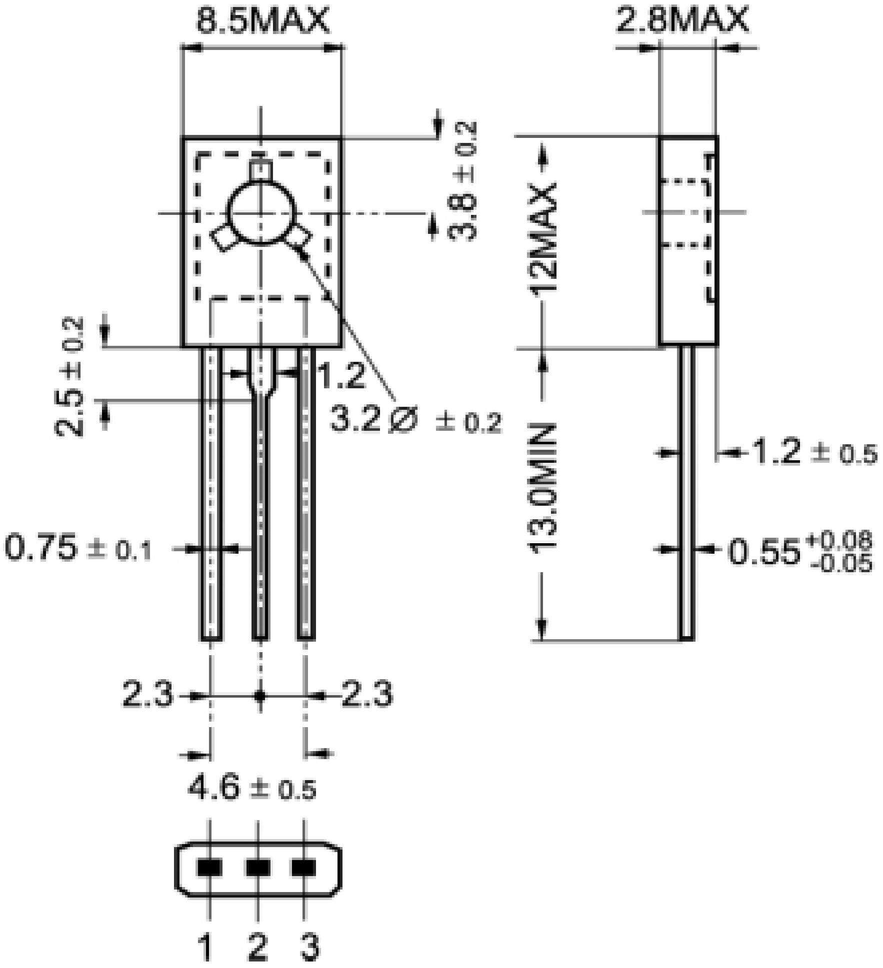

Fig.2 outline dimensions